Antonella Poggi

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

84	662	15	21
papers	citations	h-index	g-index

85	706	1.7	2.84
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
84	Processing-Induced Electrically Active Defects in Black Silicon Nanowire Devices. *ACS Applied Materials & Interfaces*, **2016**, 8, 10443-50	9.5	2
83	Rapid screening and identification of illicit drugs by IR absorption spectroscopy and gas chromatography **2013**,		4
82	Epitaxial Growth, Mechanical, Electrical Properties of SiC/Si and SiC/Poli-Si. *Materials Science Forum*, **2012**, 717-720, 897-900	0.4	
81	Non-Nitridated Oxides: Abnormal Behaviour of N-4H-SiC/SiO2 Capacitors at Low Temperature Caused by near Interface States. *Materials Science Forum*, **2011**, 679-680, 346-349	0.4	4
80	□SiC NWs Grown on Patterned and MEMS Silicon Substrates. *Materials Science Forum*, **2011**, 679-680, 508-511	0.4	1
79	The Influence of Excess Nitrogen, on the Electrical Properties of the 4H-SiC/SiO2 Interface. *Materials Science Forum*, **2011**, 679-680, 326-329	0.4	1
78	Passivation by N Implantation of the SiO2/SiC Acceptor Interface States: Impact on the Oxide Hole Traps and the Gate Oxide Reliability. *Materials Research Society Symposia Proceedings*, **2010**, 1246, 1		
77	Residual Stress Measurement and Simulation of 3C-SiC Single and Poly Crystal Cantilevers. *Materials Science Forum*, **2010**, 645-648, 865-868	0.4	3
76	Nitridation of the SiO2/SiC Interface by N+ Implantation: Hall versus Field Effect Mobility in n-Channel Planar 4H-SiC MOSFETs. *Materials Science Forum*, **2010**, 645-648, 491-494	0.4	2
75	Analysis of electron traps at the 4H□SiC/SiO2 interface; influence by nitrogen implantation prior to wet oxidation. *Journal of Applied Physics*, **2010**, 108, 024503	2.5	25
74	Effect of nitrogen implantation at the SiO2/SiC interface on the electron mobility and free carrier density in 4H-SiC metal oxide semiconductor field effect transistor channel. *Journal of Applied Physics*, **2010**, 107, 044506	2.5	15
73	Analysis of the Electron Traps at the 4H-SiC/SiO2 Interface of a Gate Oxide Obtained by Wet Oxidation of a Nitrogen Pre-Implanted Layer. *Materials Science Forum*, **2009**, 615-617, 533-536	0.4	
72	Characterization of Phosphorus Implanted n+/p Junctions Integrated as Source/Drain Regions in a 4H-SiC n-MOSFET. *Materials Science Forum*, **2009**, 615-617, 687-690	0.4	
71	Effects of N Implantation before Gate Oxidation on the Performance of 4H-SiC MOSFET. *Materials Science Forum*, **2009**, 615-617, 761-764	0.4	
70	C-V and DLTS Analyses of Trap-Induced Graded Junctions: The Case of Al+ Implanted JTE p+n 4H-SiC Diodes. *Materials Science Forum*, **2009**, 615-617, 469-472	0.4	
69	Growth and Characterization of 3C-SiC Films for Micro Electro Mechanical Systems (MEMS) Applications. *Crystal Growth and Design*, **2009**, 9, 4852-4859	3.5	32
68	Nitrogen Implantation to Improve Electron Channel Mobility in 4H-SiC MOSFET. *IEEE Transactions on Electron Devices*, **2008**, 55, 961-967	2.9	38

67	Investigation on the use of nitrogen implantation to improve the performance of n-channel enhancement 4H-SiC MOSFETs. *IEEE Transactions on Electron Devices*, **2008**, 55, 2021-2028	2.9	15
66	Improvement of Electron Channel Mobility in 4H SiC MOSFET by Using Nitrogen Implantation. *Materials Science Forum*, **2008**, 600-603, 699-702	0.4	1
65	Room Temperature Annealing Effects on Leakage Current of Ion Implanted p+n 4H-SiC Diodes. *Materials Science Forum*, **2008**, 600-603, 1027-1030	0.4	1
64	Annealing effects on leakage current and epilayer doping concentration of p+n junction 4H-SiC diodes after very high neutron irradiation. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2007**, 583, 173-176	1.2	8
63	MOS capacitors obtained by wet oxidation of n-type 4H-SiC pre-implanted with nitrogen. *Microelectronic Engineering*, **2007**, 84, 2804-2809	2.5	18
62	Effects of Very High Neutron Fluence Irradiation on p+n Junction 4H-SiC Diodes. *Materials Science Forum*, **2007**, 556-557, 917-920	0.4	5
61	Fabrication of MOS Capacitors by Wet Oxidation of p-Type 4H-SiC Preamorphized by Nitrogen Ion Implantation. *Materials Science Forum*, **2007**, 556-557, 651-654	0.4	3
60	Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. *Materials Science Forum*, **2007**, 556-557, 639-642	0.4	4
59	Analysis of the Electrical Activation of P+ Implanted Layers as a Function of the Heating Rate of the Annealing Process. *Materials Science Forum*, **2007**, 556-557, 571-574	0.4	2
58	Current Analysis of Ion Implanted p+/n 4H-SiC Junctions: Post-Implantation Annealing in Ar Ambient. *Materials Science Forum*, **2006**, 527-529, 815-818	0.4	6
57	Ion Implanted p+/n 4H-SiC Junctions: effect of the Heating Rate during Post Implantation Annealing. *Materials Research Society Symposia Proceedings*, **2006**, 911, 1		4
56	Minimum Ionizing Particle Detector Based on p+n Junction SiC Diode. *Materials Science Forum*, **2006**, 527-529, 1469-1472	0.4	1
55	Ion Implanted p+/n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. *Materials Science Forum*, **2006**, 527-529, 819-822	0.4	
54	Interfacial Properties of SiO2 Grown on 4H-SiC: Comparison between N2O and Wet O2 Oxidation Ambient. *Materials Science Forum*, **2006**, 527-529, 979-982	0.4	6
53	Correlation between Current Transport and Defects in n+/p 6H-SiC Diodes. *Materials Science Forum*, **2006**, 527-529, 811-814	0.4	2
52	Radiation hardness after very high neutron irradiation of minimum ionizing particle detectors based on 4H-SiC p/sup +/n junctions. *IEEE Transactions on Nuclear Science*, **2006**, 53, 1557-1563	1.7	47
51	Effects of heating ramp rates on the characteristics of Al implanted 4H-SiC junctions. *Applied Physics Letters*, **2006**, 88, 162106	3.4	23
50	Measurements and simulations of charge collection efficiency of p+/n junction SiC detectors. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2005**, 546, 218-221	1.2	11

49	Measurements of Charge Collection Efficiency of p+/n Junction SiC Detectors. *Materials Science Forum*, **2005**, 483-485, 1021-1024	0.4	8
48	Ar Annealing at 1600°C and 1650°C of Al+ Implanted p+/n 4H-SiC Diodes: Analysis of the J-V Characteristics Versus Annealing Temperature. *Materials Science Forum*, **2005**, 483-485, 625-628	0.4	2
47	n+/p Diodes Realized in SiC by Phosphorus Ion Implantation: Electrical Characterization as a Function of Temperature. *Materials Science Forum*, **2005**, 483-485, 649-652	0.4	1
46	Ni-Silicide Contacts to 6H-SiC: Contact Resistivity and Barrier Height on Ion Implanted n-Type and Barrier Height on p-Type Epilayer. *Materials Science Forum*, **2005**, 483-485, 737-740	0.4	3
45	Competition between Oxidation and Recrystallization in Ion Amorphized (0001) 6H-SiC. *Materials Science Forum*, **2005**, 483-485, 665-668	0.4	
44	Oxidation kinetics of ion-amorphized (0001) 6H-SiC: Competition between oxidation and recrystallization processes. *Applied Physics Letters*, **2005**, 86, 121907	3.4	12
43	The Role of the Ion Implanted Emitter State on 6H-SiC Power Diodes Behavior. A Statistical Study. *Materials Science Forum*, **2004**, 457-460, 1025-1028	0.4	1
42	SiC Donor Doping by 300°C P Implantation: Characterization of the Doped Layer Properties in Dependence of the Post-Implantation Annealing Temperature. *Materials Science Forum*, **2004**, 457-460, 945-950	0.4	5
41	Contact Resistivity and Barrier Height of Al/Ti Ohmic Contacts on p-Type Ion Implanted 4H- and 6H-SiC. *Materials Science Forum*, **2004**, 457-460, 881-884	0.4	13
40	Characterization of a Thermal Oxidation Process on SiC Preamorphized by Ar Ion Implantation. *Materials Science Forum*, **2004**, 457-460, 1357-1360	0.4	1
39	Extraction of the Schottky Barrier Height for Ti/Al Contacts on 4H-SiC from I-V and C-V Measurements. *Materials Science Forum*, **2004**, 457-460, 993-996	0.4	4
38	Structural Characterization of Alloyed Al/Ti and Ti Contacts on SiC. *Materials Science Forum*, **2004**, 457-460, 837-840	0.4	10
37	Low temperature oxidation of SiC preamorphized by ion implantation. *Journal of Applied Physics*, **2004**, 95, 6119-6123	2.5	14
36	Improved electrical characterization of Al/Ti ohmic contacts on p-type ion implanted 6H-SiC. *Semiconductor Science and Technology*, **2003**, 18, 554-559	1.8	25
35	Al/Ti Ohmic Contacts to p-Type Ion-Implanted 6H-SiC: Mono- and Two- Dimensional Analysis of TLM Data. *Materials Science Forum*, **2003**, 433-436, 673-676	0.4	7
34	Low-Temperature Thermal Oxidation of Ion-Amorphized 6H-SiC. *Materials Science Forum*, **2002**, 389-393, 1109-1112	0.4	8
33	A Comparative Study of High-Temperature Aluminum Post-Implantation Annealing in 6H- and 4H-SiC, Non-Uniform Temperature Effects. *Materials Science Forum*, **2002**, 389-393, 827-830	0.4	11
32	Contact resistivity of Al/Ti ohmic contacts on p-type ion implanted 4H- and 6H-SiC.. *Materials Research Society Symposia Proceedings*, **2002**, 742, 621		11

31	TEM characterisation of porous silicon. *Micron*, **2000**, 31, 223-30	2.3	24
30	Composition and structure of tin/vanadium oxide surfaces for chemical sensing applications. *Sensors and Actuators B: Chemical*, **2000**, 71, 123-126	8.5	32
29	Permeated Porous Silicon Suspended Membrane as Sub-ppm Benzene Sensor for Air Quality Monitoring. *Journal of Porous Materials*, **2000**, 7, 197-200	2.4	17
28	Permeated porous silicon for hydrocarbon sensor fabrication. *Sensors and Actuators A: Physical*, **1999**, 74, 95-99	3.9	42
27	microstructural development in pure and V-doped SnO2 nanopowders. *Journal of the European Ceramic Society*, **1999**, 19, 2073-2077	6	11
26	Thick oxidised porous silicon layer as a thermo-insulating membrane for high-temperature operating thin- and thick-film gas sensors. *Sensors and Actuators B: Chemical*, **1998**, 49, 22-29	8.5	21
25	Deep level transient spectroscopy study of the damage induced in n-type silicon by a gate oxide etching in a CHF3/Ar plasma. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1997**, 15, 623		7
24	Porous silicon layer permeated with SnV mixed oxides for hydrocarbon sensor fabrication. *Thin Solid Films*, **1997**, 297, 43-47	2.2	16
23	Surface damage in processed silicon. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1996**, 42, 249-253	3.1	2
22	Electrical Properties of Silver Impurities and their Annealing Behaviour in p-Type Fz Silicon. *Journal De Physique III*, **1996**, 6, 1691-1696		4
21	Electrical Properties of Rapid Thermal Annealing Induced Defects in Silicon. *Journal of the Electrochemical Society*, **1995**, 142, 2081-2085	3.9	5
20	Study of the electrical active defects induced by reactive ion etching in n-type silicon. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1995**, 13, 2139		3
19	Rapid Thermal Annealing of p-Type Silicon: Correlation Between Deep-Level Transient Spectroscopy and Lifetime Measurements. *Journal of the Electrochemical Society*, **1994**, 141, 754-758	3.9	6
18	Copper impurities and their annealing behaviour in FZ silicon. *Physica Status Solidi A*, **1994**, 143, 373-377		6
17	Arsenic ion implantation through Mo and Mo silicide layers for shallow junction formation. *Solid-State Electronics*, **1992**, 35, 941-947	1.7	1
16	Shallow junction formation using MoSi2 as diffusion source. *Microelectronic Engineering*, **1992**, 19, 673-676	2.5	1
15	On the Connection Between Interstitial Oxygen, Oxygen Precipitate, and Diffusions of Cr and Cu Impurities in Cz Silicon. *Physica Status Solidi A*, **1991**, 123, K1-K6		
14	B-Ion Implantation into Mo-Film for Shallow Junction Formation: DLTS Analyses on the p+/n Fabricated Diodes. *Solid State Phenomena*, **1991**, 19-20, 505-510	0.4	

13	Effect of Rapid Thermal Annealing on Electrical and Structural Properties of Silicon. *Journal of the Electrochemical Society*, **1991**, 138, 1841-1845	3.9	3
12	Boron ion implantation through Mo and Mo silicide layers for shallow junction formation. *Journal of Applied Physics*, **1991**, 69, 3962-3967	2.5	6
11	Some electrical characteristics of Fe and its annealing behaviour in FZ silicon. *Physica Status Solidi A*, **1990**, 118, 491-496		6
10	Intrinsic gettering of Cr impurities in p-type Cz silicon. *Physica Status Solidi A*, **1990**, 121, 181-185		2
9	Effects of silicon ion-beam mixing on p+/n diodes: DLTS analyses of the induced defects. *Physica Status Solidi A*, **1990**, 121, K135-K139		
8	RTA-induced defects: a comparison between lamp and electron beam techniques. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1989**, 4, 231-235	3.1	2
7	Schottky contact barrier height enhancement on p-type silicon by wet chemical etching. *Applied Physics A: Solids and Surfaces*, **1989**, 48, 391-395		6
6	The electrical activity of stacking faults in Czochralski silicon. *Applied Physics A: Solids and Surfaces*, **1989**, 48, 431-436		4
5	Effect of passivating oxides on the surface recombination velocity in silicon. *Physica Status Solidi A*, **1989**, 113, K61-K65		1
4	The Effects of High Temperature Anneal on the Electrical Activity of Iron in B-Doped Cz Silicon. *Physica Status Solidi A*, **1989**, 114, 247-252		
3	Lifetime and crystal order in annealed CZ silicon. *Physica Status Solidi A*, **1988**, 108, 503-508		2
2	Denuded zone stability in a SPAD diode as a function of out-diffusion parameters. *IEEE Transactions on Electron Devices*, **1987**, 34, 1496-1500	2.9	3
1	Lattice disorder and recombination centres in heat-treated FZ silicon. *Physica Status Solidi A*, **1985**, 92, 177-185		9